

Amendments to the specification:

Please replace the paragraph which begins at page 3, line 33 and ends at page 3 line 37 with the amended paragraph below:

-- It is advantageous that the etching rate achieved with the solutions according to the invention for the etching of PSG layers, BSG layers and **BBSG BPSG** layers is a multiple higher (up to >300) than for TEOS layers or layers of thermal oxide. --